



UK4145

Power MOSFET

SWITCHING N-CHANNEL POWER MOSFET

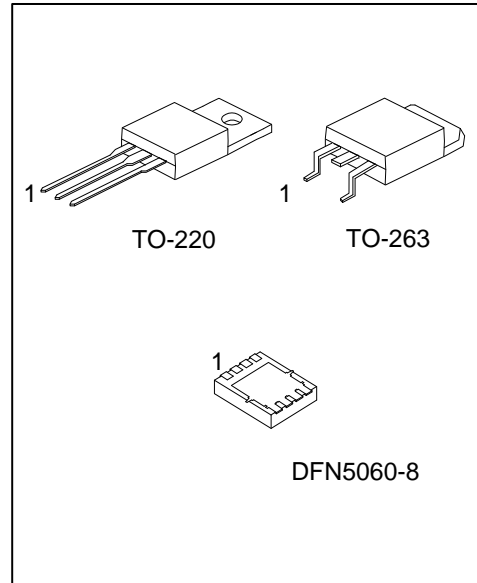
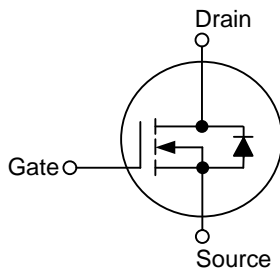
DESCRIPTION

The UTC **UK4145** is N-channel power MOSFET, suitable for high current switching applications.

FEATURES

- * Low on-state resistance:
 $R_{DS(ON)} \leq 10 \text{ m}\Omega @ V_{GS}=10V, I_D=42A$

SYMBOL



ORDERING INFORMATION

Ordering Number		Package	Pin Assignment						Packing		
Lead Free	Halogen Free		1	2	3	4	5	6		7	8
UK4145L-TA3-T	UK4145G-TA3-T	TO-220	G	D	S	-	-	-	-	-	Tube
UK4145L-TQ2-T	UK4145G-TQ2-T	TO-263	G	D	S	-	-	-	-	-	Tube
UK4145L-TQ2-R	UK4145G-TQ2-R	TO-263	G	D	S	-	-	-	-	-	Tape Reel
UK4145L-K08-5060-R	UK4145G-K08-5060-R	DFN5060-8	S	S	S	G	D	D	D	D	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>UK4145G-TA3-T</p>	<p>(1) T: Tube, R: Tape Reel (2) TA3: TO-220, TQ2: TO-263 K08-5060: DFN5060-8 (3) G: Halogen Free and Lead Free, L: Lead Free</p>
----------------------	--

MARKING

TO-220 / TO-263	DFN5060-8

■ **ABSOLUTE MAXIMUM RATINGS** ($T_A=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT	
Drain-Source Voltage ($V_{GS}=0\text{ V}$)	V_{DSS}	60	V	
Gate-Source Voltage ($V_{DS}=0\text{ V}$)	V_{GSS}	± 20	V	
Drain Current	DC ($T_C=25^\circ\text{C}$)	I_D	84	A
	Pulse (Note 2)	I_{DM}	215	A
Single Avalanche Current (Note 4)	I_{AS}	63.6	A	
Single Avalanche Energy (Note 4)	E_{AS}	202	mJ	
Power Dissipation ($T_A=25^\circ\text{C}$)	TO-220/TO-263	P_D	2	W
	DFN5060-8		1.5	W
Junction Temperature	T_J	+150	$^\circ\text{C}$	
Strong Temperature	T_{STG}	-55 ~ +150	$^\circ\text{C}$	

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature.
3. $L=100\mu\text{H}$, $I_{AS}=6.5\text{A}$, $V_{DD}=30\text{V}$, $R_G=25\ \Omega$, $V_{GS}=20\text{V}$, Starting $T_J=25^\circ\text{C}$
4. $P_W \leq 10\mu\text{s}$, Duty Cycle $\leq 1\%$.

■ **THERMAL DATA**

PARAMETER	SYMBOL	RATINGS	UNIT	
Junction to Ambient	TO-220/TO-263	θ_{JA}	62.5	$^\circ\text{C/W}$
	DFN5060-8		83.3 (Note)	$^\circ\text{C/W}$
Junction to Case	TO-220/TO-263	θ_{JC}	1.25	$^\circ\text{C/W}$
	DFN5060-8		5.43 (Note)	$^\circ\text{C/W}$

Note: Device mounted on FR-4 substrate P_C board, 2oz copper, with 1inch square copper plate.

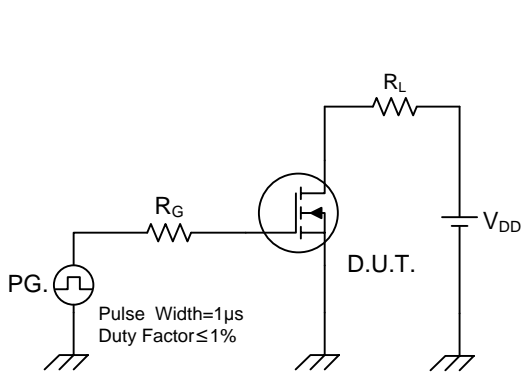
■ **ELECTRICAL CHARACTERISTICS** ($T_J = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	60			
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 60V, V_{GS} = 0V$			1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(OFF)}$	$V_{DS} = 10V, I_D = 1mA$	2.0	3.0	4.0	V
Drain to Source On-state Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 42A$		7	10	m Ω
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{DS} = 10V, V_{GS} = 0V, f = 1MHz$		3900		pF
Output Capacitance	C_{OSS}			625		Pf
Reverse Transfer Capacitance	C_{RSS}			475		pF
SWITCHING PARAMETERS						
Total Gate Charge	Q_G	$V_{DS} = 48V, V_{GS} = 10V, I_D = 42A, I_G = 1mA$ (Note 1, 2)		82		nC
Gate Source Charge	Q_{GS}			12		nC
Gate Drain Charge	Q_{GD}			21		nC
Turn-ON Delay Time	$t_{D(ON)}$	$V_{DD} = 30V, V_{GS} = 10V, I_D = 42A,$ $R_G = 25\Omega$ (Note 1, 2)		15		ns
Turn-ON Rise Time	t_R			20		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			54		ns
Turn-OFF Fall-Time	t_F			27		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Continuous Drain-Source Diode Forward Current	I_S				84	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				215	A
Drain-Source Diode Forward Voltage (Note)	V_{SD}	$V_{GS} = 0V, I_S = 84A$		1.0	1.5	V
Reverse Recovery Time	t_{rr}	$V_{GS} = 0V, I_S = 84A, di/dt = 100A/\mu s$		43		ns
Reverse Recovery Charge	Q_{rr}			50		nC

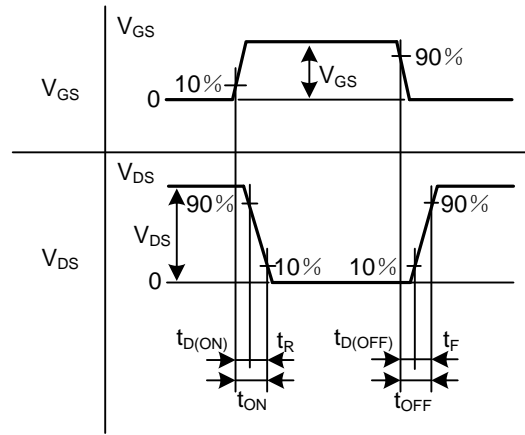
Notes: 1. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

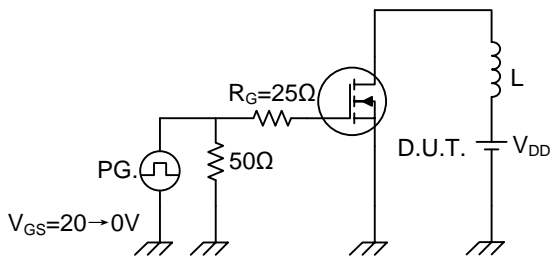
■ TEST CIRCUITS AND WAVEFORMS



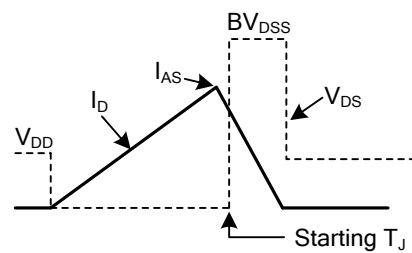
Switching Test Circuit



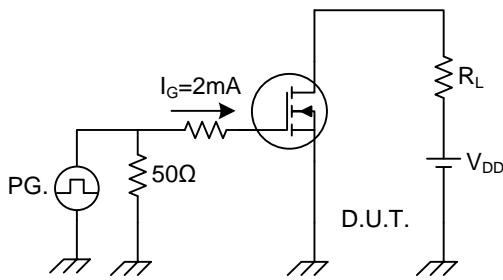
Switching Waveforms



Unclamped Inductive Switching Test Circuit

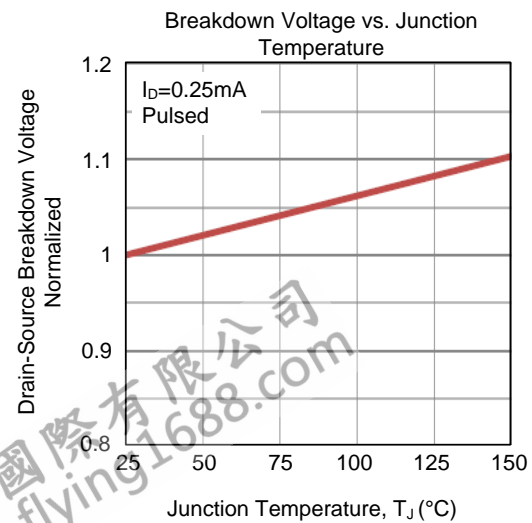
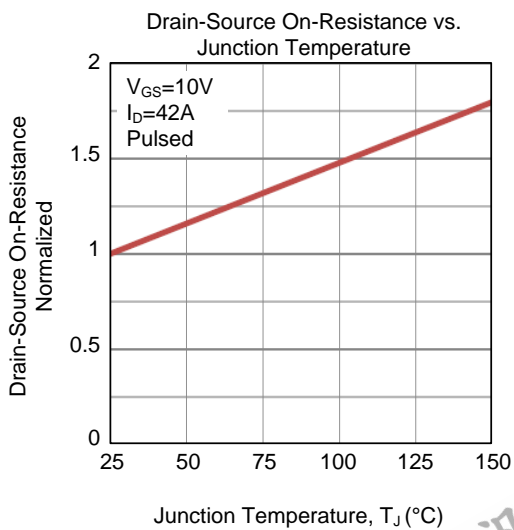
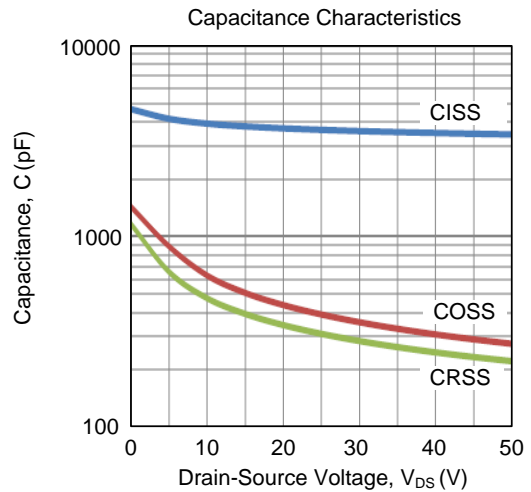
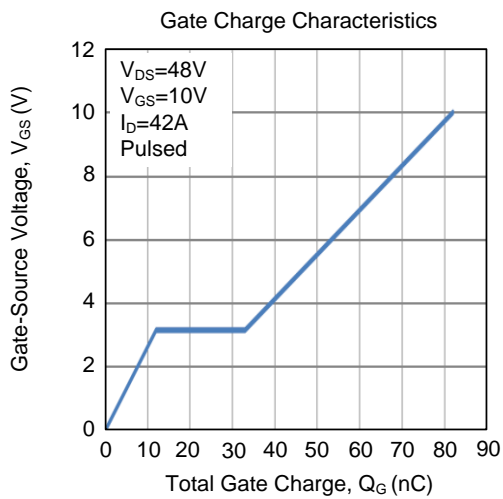
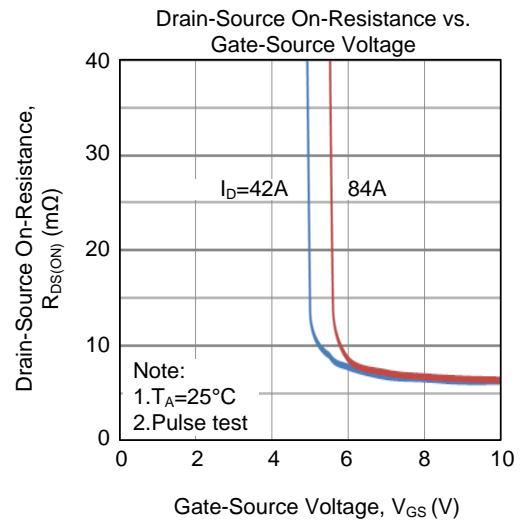
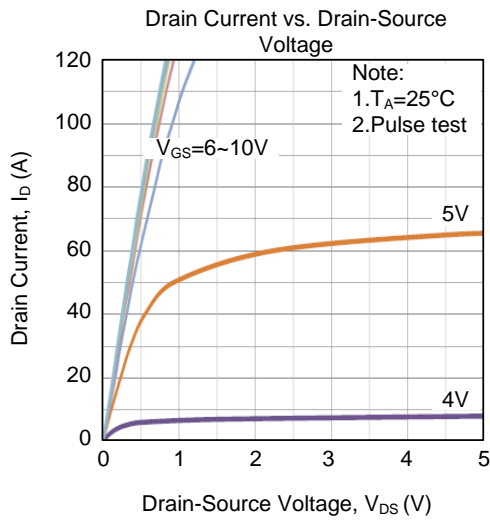


Unclamped Inductive Switching Waveforms

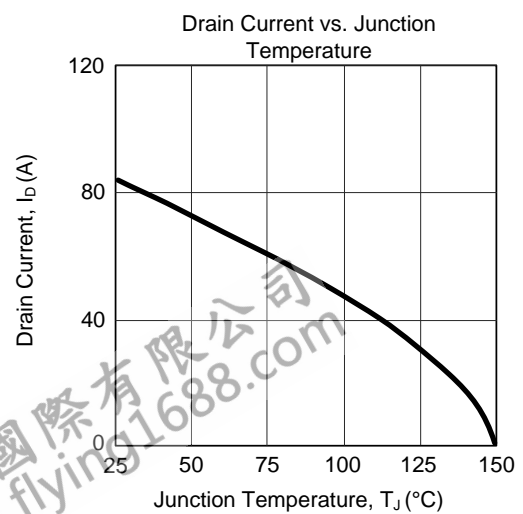
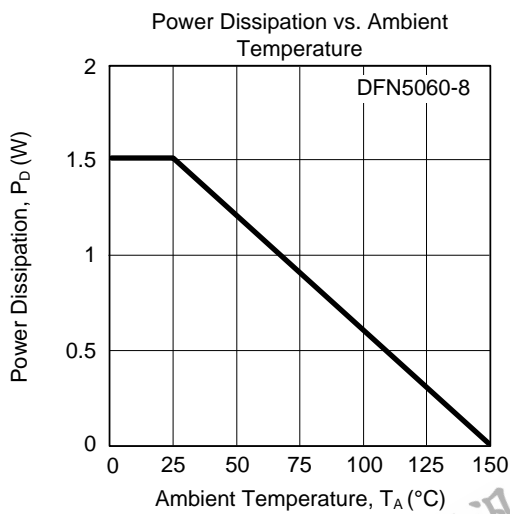
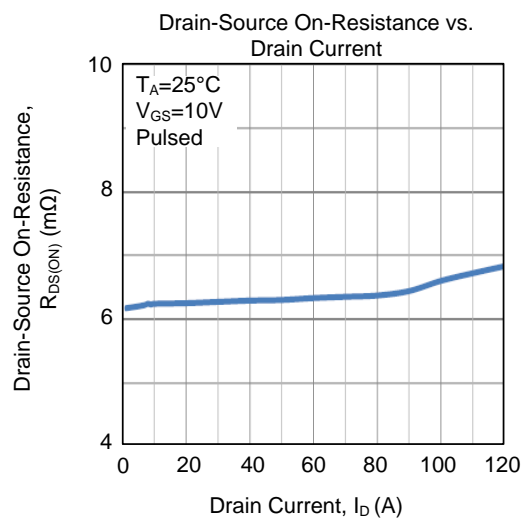
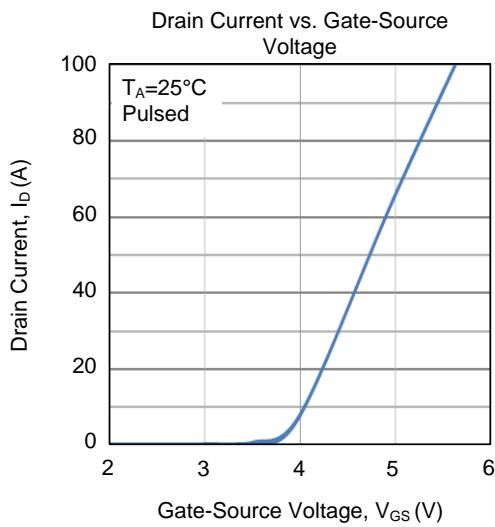
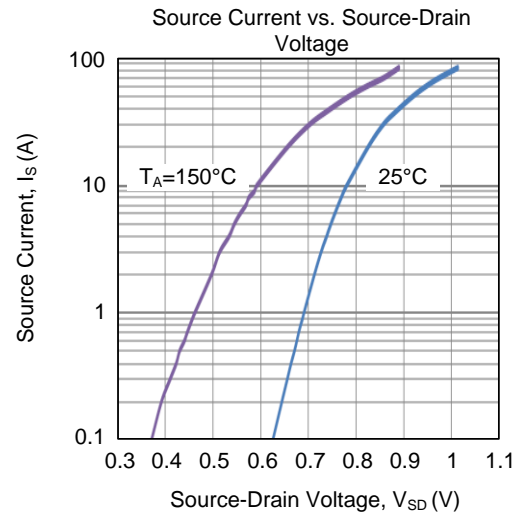
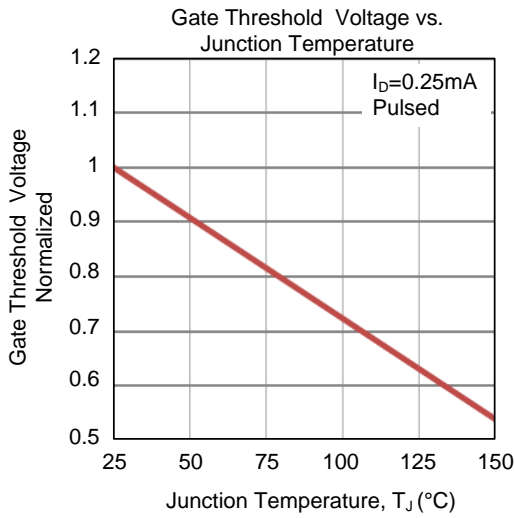


Gate Charge Test Circuit

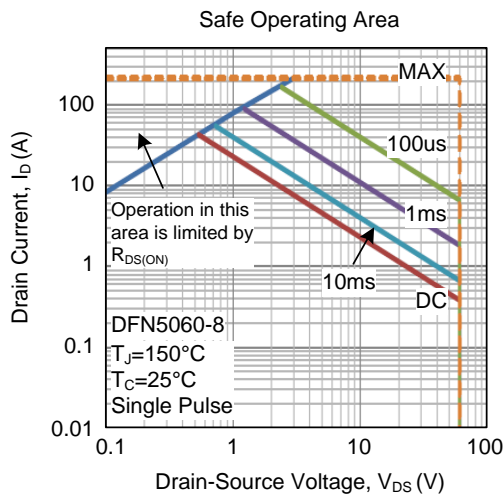
■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



■ **TYPICAL CHARACTERISTICS (Cont.)**



UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. UTC reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.